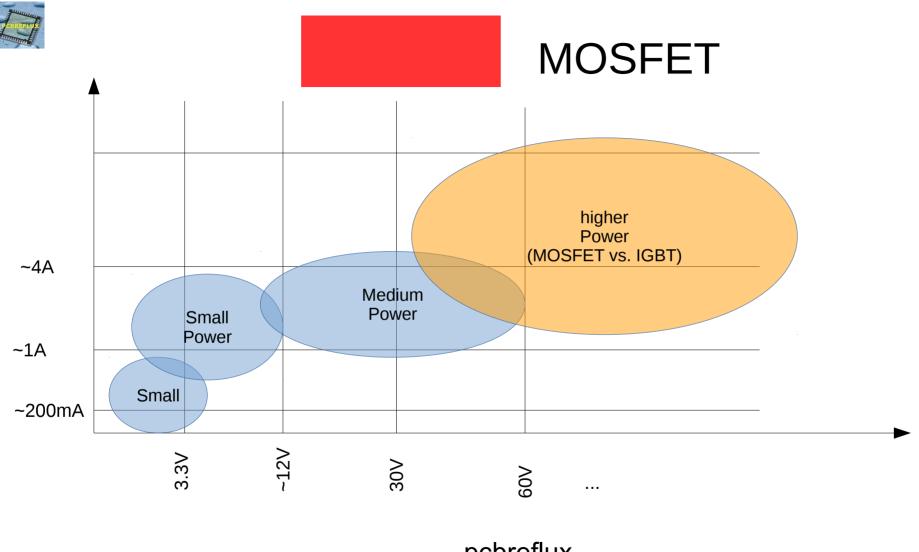




MOSFET metal-oxide-semiconductor field-effect transistor

depletion mode and enhancement mode

Using the MOSFET as a Switch (< 1kHz)



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Important Parameter

I_D Continuous Drain Current

 $V_{\text{GS(th)}}$ Gate Threshold Voltage

 V_{GS} Gate-Source Voltage

V_{DS} Drain-Source Voltage

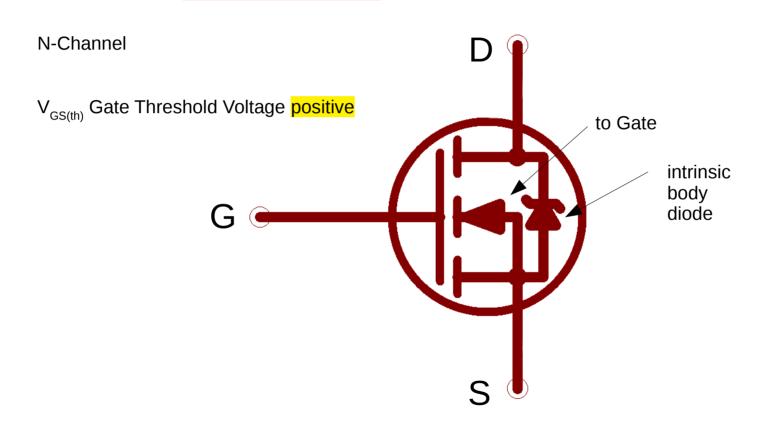
 $R_{\mathrm{DS(ON)}}$ Drain-Source On-Resistance

Thermal considerations

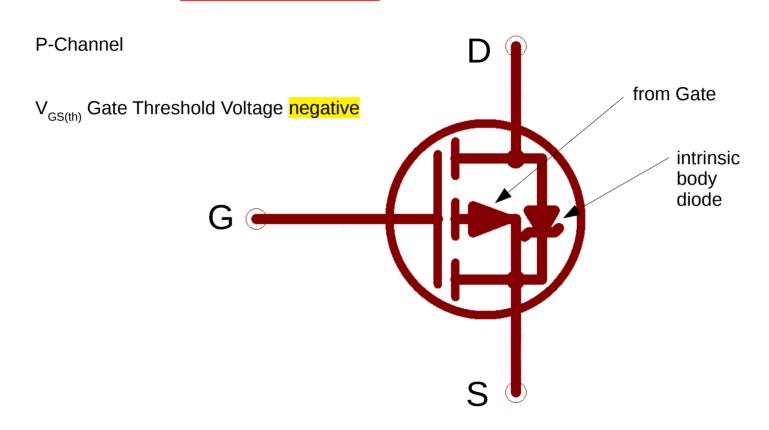
P_D Power Dissipation

 $R_{\theta JA} (R_{THJA})$ Junction-to-Ambient

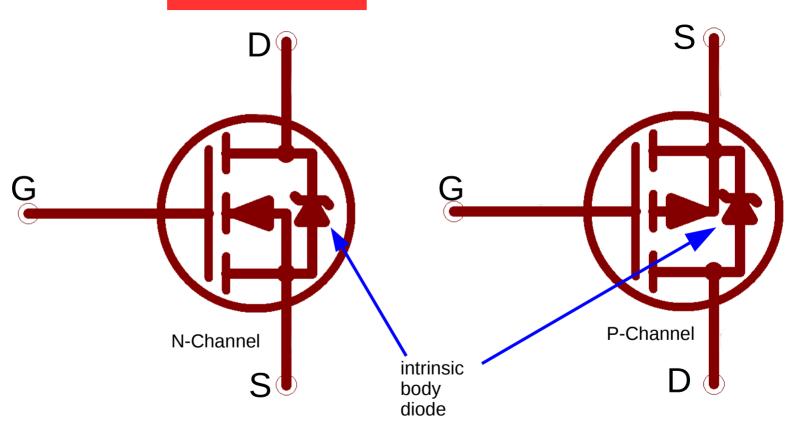




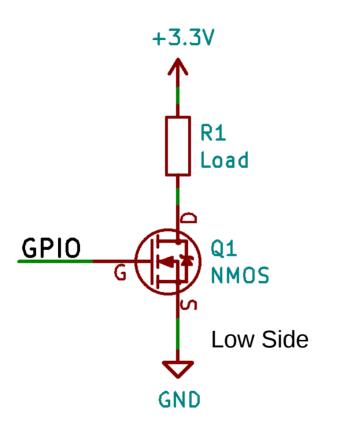


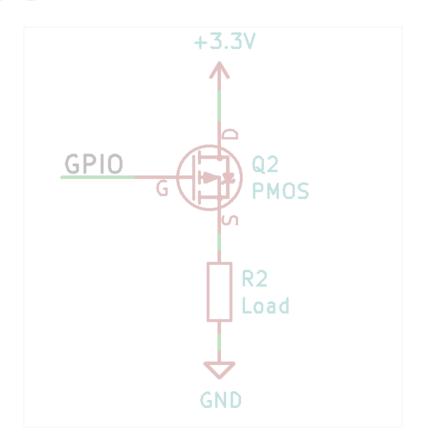






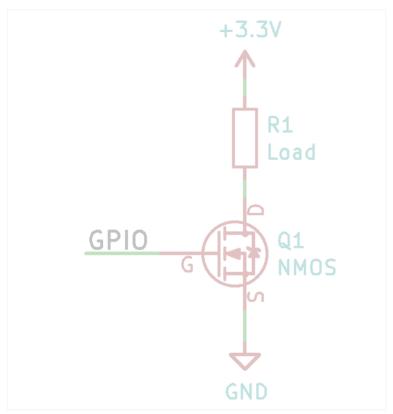


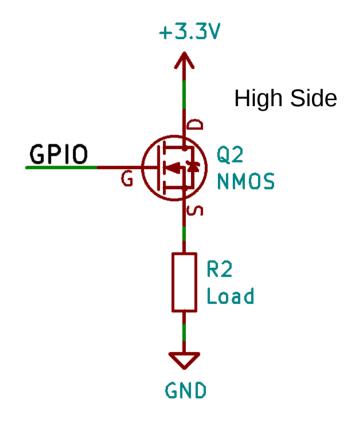








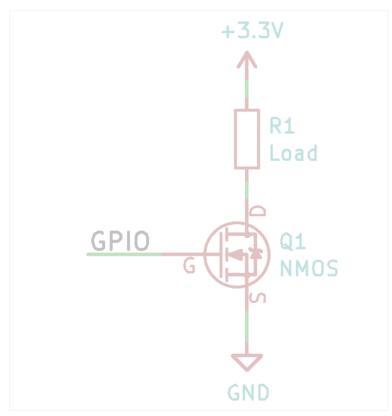


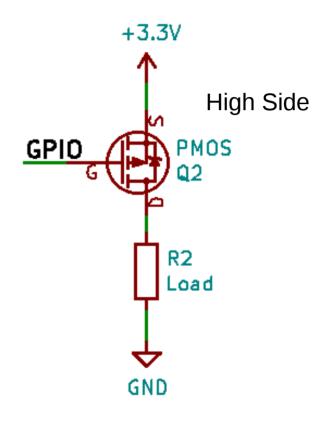


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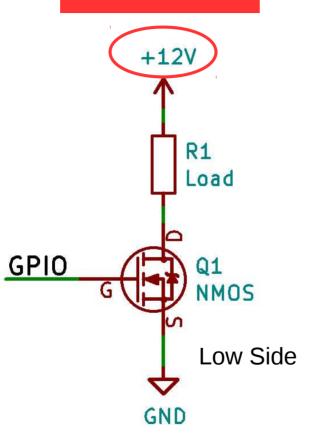


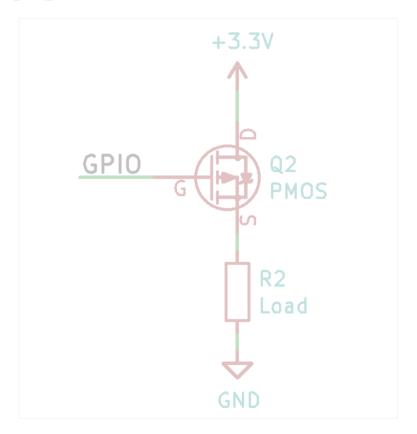




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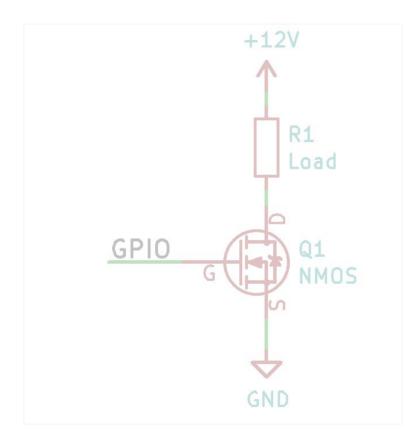


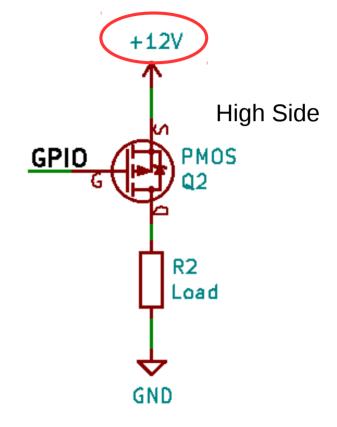








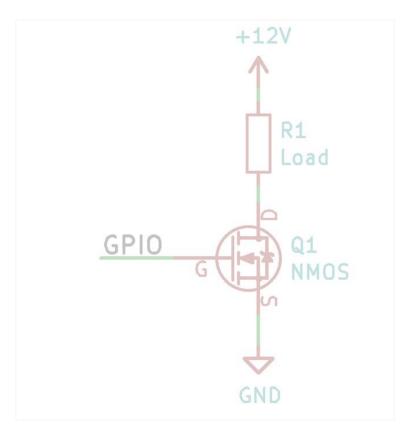


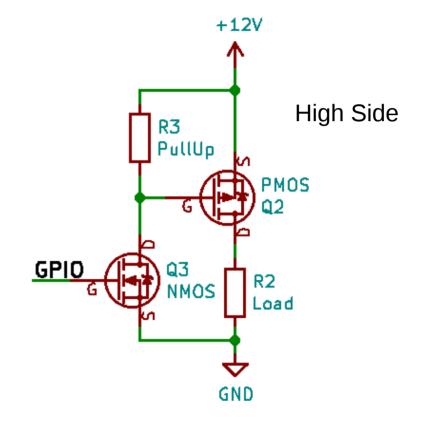


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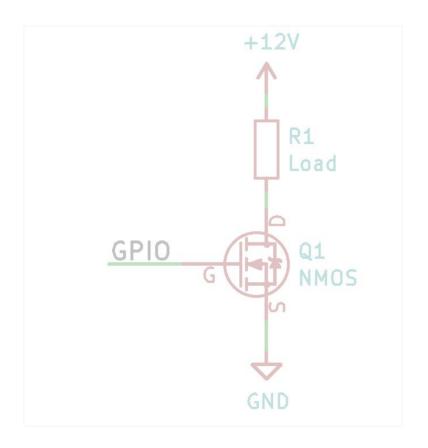


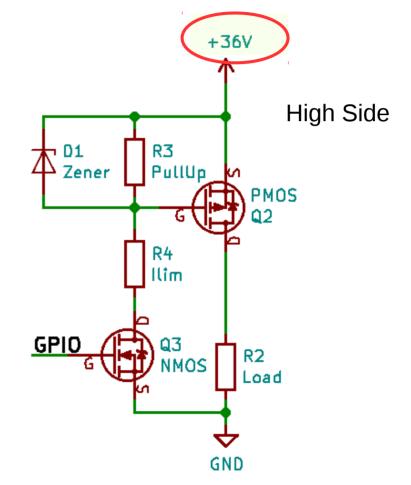


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ESP32





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Thermal Example IRFU9024 (IPAK)

Example Drain Current : 2A

 $R_{DS(ON)}$ Drain-Source On-Resistance Max 0.28Ω

P_D Power Dissipation
$$I_D^2 * R_{DS(ON)} = (2A)^2 * 0.28\Omega = 1.12 W$$

R_{A1A} Junction-to-Ambient 110°C/W in Air and 50°C/W on PCB

$$P_{\text{JMAX}} = (T_{\text{JMAX}} - T_{\text{A}}) / R_{\theta \text{JA}} (150^{\circ}\text{C} - 25^{\circ}\text{C}) / 110^{\circ}\text{C/W} \sim 1.136 \text{ W in Air}$$
 (150°C-25°C) / 50°C/W ~ 2.5 W on PCB

→ in Air (1.12W ~ 1.136W) nearly needs heatsink on PCB (1.12W < 2.5W) no heatsink needed</p>





Thermal Example DMG2301L (SOT23)

Example Drain Current: 2A

 $R_{DS(ON)}$ Drain-Source On-Resistance Max 0.12Ω

 P_D Power Dissipation $I_D^2 * R_{DS(ON)} = (2A)^2 * 0.12\Omega = 0.48W$

 $R_{\theta JA}$ Junction-to-Ambient 83°C/W

 $P_{JMAX} = (T_{JMAX} - T_A) / R_{\theta JA} (150^{\circ}C - 25^{\circ}C) / 83^{\circ}C/W \sim 1.5 W$

0.48W < 1.5W → no heatsink needed